

Georges Landa

List of Publications by Year in descending order

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65
papers

1,087
citations

430754

18
h-index

454834

30
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66
all docs

66
docs citations

66
times ranked

1165
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhancing DFT-based energy landscape exploration by coupling Quantum Mechanics and Static Modes. <i>Physical Chemistry Chemical Physics</i> , 2022, 24, 12011-12026.	1.3	0
2	Finding Reaction Pathways and Transition States: r-ARTn and d-ARTn as an Efficient and Versatile Alternative to String Approaches. <i>Journal of Chemical Theory and Computation</i> , 2020, 16, 6726-6734.	2.3	21
3	Water Distribution within Wild-Type NRas Protein and Q61 Mutants during Unrestrained QM/MM Dynamics. <i>Biophysical Journal</i> , 2018, 115, 1417-1430.	0.2	10
4	A perfect wetting of Mg monolayer on Ag(111) under atomic scale investigation: First principles calculations, scanning tunneling microscopy, and Auger spectroscopy. <i>Journal of Chemical Physics</i> , 2016, 144, 194708.	1.2	1
5	Toward in Silico Biomolecular Manipulation through Static Modes: Atomic Scale Characterization of HIV-1 Protease Flexibility. <i>Journal of Physical Chemistry B</i> , 2014, 118, 2821-2830.	1.2	2
6	Bringing aptamers into technologies: Impact of spacer terminations. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	4
7	Oxidation of Germanium and Silicon surfaces (100): a comparative study through DFT methodology. <i>IOP Conference Series: Materials Science and Engineering</i> , 2012, 41, 012007.	0.3	9
8	A computational chemist approach to gas sensors: Modeling the response of SnO ₂ to CO, O ₂ , and H ₂ O Gases. <i>Journal of Computational Chemistry</i> , 2012, 33, 247-258.	1.5	42
9	Tail effect on trihydroxysilanes dimerization: A dispersion-corrected density functional theory study. <i>Surface Science</i> , 2012, 606, 7-11.	0.8	2
10	Mimicking DNA stretching with the Static Mode method: Shear stress versus transverse pulling stress. <i>European Physical Journal E</i> , 2012, 35, 75.	0.7	3
11	Introducing densification mechanisms into the modelling of HfO ₂ atomic layer deposition. <i>Thin Solid Films</i> , 2012, 520, 4559-4563.	0.8	10
12	The electrostatic probe: a tool for the investigation of the A β (1-16) peptide deformations using the static modes. <i>Physical Chemistry Chemical Physics</i> , 2011, 13, 14611.	1.3	2
13	Atomic Scale Determination of Enzyme Flexibility and Active Site Stability through Static Modes: Case of Dihydrofolate Reductase. <i>Journal of Physical Chemistry B</i> , 2011, 115, 1616-1622.	1.2	6
14	Stability of Frenkel pairs in Si(100) surface in the presence of germanium and oxygen atoms. <i>Microelectronic Engineering</i> , 2011, 88, 503-505.	1.1	0
15	Atomic-scale determination of DNA conformational response to strained furanose: a static mode approach. <i>Tetrahedron</i> , 2010, 66, 9123-9128.	1.0	4
16	Deformation of thiolated nucleic acid deposited on a silicon surface: A Static Mode approach. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010, 169, 23-27.	1.7	4
17	A mesoscopic model of the intermixing during nanoenergetic materials processing. <i>Journal of Physics and Chemistry of Solids</i> , 2010, 71, 125-129.	1.9	5
18	Periodic boundary versus quantum cluster approaches in the simulation of a nanoenergetic metallic model-system: Ni/Al(111) surface reactions. <i>Journal of Physics and Chemistry of Solids</i> , 2010, 71, 130-133.	1.9	3

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19	First-principles study of near surface point defects stability in Si (100) and SiGe(100). <i>Thin Solid Films</i> , 2010, 518, 2418-2421.	0.8	3
20	Asymmetric diffusion as a key mechanism in Ni/Al energetic multilayer processing: A first principles study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2010, 28, L15-L17.	0.9	16
21	A kinetic Monte Carlo study of the initial stage of silicon oxidation: Basic mechanisms-induced partial ordering of the oxide interfacial layer. <i>Surface Science</i> , 2009, 603, 2132-2137.	0.8	12
22	Evidence of the Ge nonreactivity during the initial stage of SiGe oxidation. <i>Applied Physics Letters</i> , 2009, 94, 041912.	1.5	10
23	The Static Modes: An alternative approach for the treatment of macro- and bio-molecular induced-fit flexibility. <i>European Physical Journal E</i> , 2009, 28, 17-25.	0.7	7
24	Evidence of Self-Assembled Monolayers Preorganization Prior to Surface Contact: a First Principles Study. <i>Journal of Physical Chemistry C</i> , 2009, 113, 15652-15657.	1.5	6
25	Insights into Crystalline Preorganization of Gas-Phase Precursors: Densification Mechanisms. <i>Chemistry of Materials</i> , 2008, 20, 1555-1560.	3.2	18
26	A new insight into the understanding of the collapsed form of poly(N-isopropylacrylamide) molecules. <i>Chemical Physics</i> , 2007, 340, 12-16.	0.9	8
27	Substrate size effects in the modeling of molecular grafting: Case of organo-silane chains on silica. <i>Chemical Physics</i> , 2006, 323, 179-184.	0.9	11
28	Nanoscale pressure effects in individual double-wall carbon nanotubes. <i>Physical Review B</i> , 2006, 73, .	1.1	32
29	Spectroscopic detection of carbon nanotube interaction with amphiphilic molecules in epoxy resin composites. <i>Journal of Applied Physics</i> , 2005, 97, 034303.	1.1	26
30	Role of the substrate imperfections on the island nucleation and defect formation: case of GaSb/GaAs(001). <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 88, 181-185.	1.7	5
31	Kinetic Monte Carlo simulation of intermixing during semiconductor heteroepitaxy. <i>Applied Surface Science</i> , 2002, 188, 24-28.	3.1	3
32	Ge clusters in Si matrix: structure and dynamics. <i>European Physical Journal B</i> , 1999, 12, 343-346.	0.6	3
33	Dislocation half loop formation in GaSb/(001)GaAs islands and steps role: a Monte Carlo simulation. <i>Thin Solid Films</i> , 1998, 336, 277-280.	0.8	2
34	Beyond the solid on solid model: An atomic dislocation formation mechanism. <i>Journal of Applied Physics</i> , 1998, 84, 5487-5494.	1.1	14
35	Optical-phonon behavior in Ga _{1-x} In _x As: The role of microscopic strains and ionic plasmon coupling. <i>Physical Review B</i> , 1998, 58, 10452-10462.	1.1	101
36	Strain effects on optical phonons in GaAs layers analyzed by Raman scattering. <i>Journal of Applied Physics</i> , 1997, 82, 4493-4499.	1.1	17

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37	Tensile and compressive strain relief in $\text{In}_x\text{Ga}_{1-x}\text{As}$ epilayers grown on InP probed by Raman scattering. Journal of Applied Physics, 1997, 82, 803-809.	1.1	55
38	MBE growth and Raman analysis of $[\text{hhk}]\text{GaAs}/(\text{Si or CaF}_2)$ highly strained hetero-structures. Microelectronics Journal, 1995, 26, 789-795.	1.1	6
39	Strain relaxation in $[\text{001}]$ and $[\text{111}]\text{GaAs}/\text{CaF}_2$ analyzed by Raman spectroscopy. Journal of Applied Physics, 1995, 77, 1126-1132.	1.1	17
40	Raman scattering study of $[\text{hhk}]\text{GaAs}/(\text{Si or CaF}_2)$ strained heterostructures. Journal of Applied Physics, 1994, 76, 2773-2780.	1.1	12
41	Long-wavelength optical phonons of $\text{Cd}_x\text{Zn}_{1-x}\text{Sb}$ mixed crystals. Semiconductor Science and Technology, 1994, 9, 333-337.	1.0	9
42	Low wavenumber Raman scattering in viscous liquids. Journal of Raman Spectroscopy, 1994, 25, 849-854.	1.2	8
43	Raman scattering in $\text{Ge-Ge}_{1-x}\text{Six}$ superlattice. Superlattices and Microstructures, 1993, 13, 109-114.	1.4	5
44	Dynamical properties of $\text{Ga}_{1-x}\text{In}_x\text{As}$ solid solutions: Influence of local distortion effects. Solid State Communications, 1993, 86, 351-355.	0.9	26
45	Raman study of longitudinal optical phonon-plasmon coupling and disorder effects in heavily Be-doped GaAs. Journal of Applied Physics, 1991, 69, 4064-4070.	1.1	65
46	GaSb/GaAs heteroepitaxy characterized as a stress-free system. Applied Surface Science, 1991, 50, 434-439.	3.1	22
47	Raman study under resonant conditions of defects near the interface in a GaAs/Si heterostructure. Journal of Applied Physics, 1990, 68, 4777-4781.	1.1	23
48	Caractérisation Raman des contraintes et des défauts d'interface dans GaAs/Si. Revue De Physique Appliquée, 1990, 25, 951-956.	0.4	0
49	Photoluminescence and Raman studies of residual stresses in GaAs directly grown on InP. Applied Physics Letters, 1989, 55, 1558-1560.	1.5	16
50	Optical determination of strains in heterostructures: GaAs/Si as an example. Journal of Applied Physics, 1989, 66, 196-200.	1.1	71
51	Influence of MOVPE growth parameters on the structural and optical properties of GaAs on Si(100). Journal of Crystal Growth, 1988, 93, 487-493.	0.7	22
52	Raman determination of the composition in semiconductor ternary solid solutions. Journal of Applied Physics, 1987, 61, 1206-1208.	1.1	34
53	Raman scattering analysis of disorder in heterogeneous $(\text{GaAs})_{1-x}(\text{SiC}_2\text{H})_x$ films grown by metal-organic chemical vapour deposition. Thin Solid Films, 1987, 155, 331-342.	0.8	9
54	Microstructure of boron-doped silicon layers prepared by low pressure chemical vapour deposition. Thin Solid Films, 1987, 150, 69-82.	0.8	8

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55	Characterization of implantation and annealing of Zn-implanted InP by Raman spectrometry. Journal of Applied Physics, 1986, 60, 1980-1984.	1.1	47
56	Molecular-beam epitaxy and optical characterization of GaAs on CaF ₂ substrates. Journal of Applied Physics, 1986, 60, 208-212.	1.1	14
57	Raman characterization of twinning in heteroepitaxial semiconductor layers: GaAs/(Ca,Sr)F ₂ . Journal of Applied Physics, 1986, 60, 1025-1031.	1.1	31
58	Raman investigation of the InP lattice dynamics. Journal of Physics C: Solid State Physics, 1986, 19, 1471-1479.	1.5	55
59	Bond relaxation phenomenon and impurity modes frequencies in III-V compounds. Solid State Communications, 1985, 53, 179-182.	0.9	21
60	Comportement de deux modes de Ga(x)In(1-x)P ? Diffusion Raman résonnante par les modes rendus actifs par le désordre. Revue De Physique Appliquée, 1984, 19, 17-20.	0.4	14
61	Lattice dynamics of the transition metal pentatellurides ZrTe ₅ and HfTe ₅ . Solid State Communications, 1984, 50, 297-302.	0.9	14
62	Lacking Raman spectroscopic evidence for a structural phase transition in ZrTe ₅ at 141 K. Solid State Communications, 1984, 49, 1095-1098.	0.9	10
63	Phonons in the ternary phase ZrS _{3-x} Sex. Solid State Communications, 1983, 45, 889-893.	0.9	15
64	Raman scattering in the ternary phase HfS _{3-x} Sex. Physical Review B, 1982, 26, 5694-5701.	1.1	20
65	Lattice modes in the linear chain compound ZrTe ₅ . Solid State Communications, 1982, 44, 89-94.	0.9	15